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Docket: 0756-711

Date: March 17, 1992

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

Sir:

Transmitted herewith for filing is the Rule 53(b) Patent
Application of:

1-00 et al
Inventor(s): Shunpei YAMAZAKI
Hongyong ZHANG
Naoto KUSUMOTO
Yasuhiko TAKEMURA

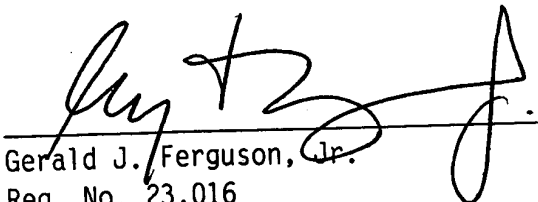
For: SEMICONDUCTOR MATERIAL AND METHOD FOR
FORMING THE SAME AND THIN FILM TRANSISTOR

Enclosed are:

[X] 33 pages of specification and claims
[X] 6 sheets of drawings () formal (X) informal

[X] Priority is claimed based on foreign application(s)
No(s): 3-80799
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Respectfully submitted,


Gerald J. Ferguson, Jr.
Reg. No. 23,016

Sixbey, Friedman, Leedom & Ferguson, P.C.
2010 Corporate Ridge, Suite 600
McLean, Virginia 22102
(703) 790-9110

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

INVENTORS: Shunpei YAMAZAKI
21-21, Kitakarasuyama, 7-chome
Setagaya-ku, Tokyo 157 Japan

Hongyong ZHANG
Paresu Miyagami 302, 1-10-15, Fukamidai
Yamato-shi, Kanagawa-ken, 242 Japan

Naoto KUSUMOTO
Flat SEL-B 202, 304-1, Hase, Atsugi-shi
Kanagawa-ken, 243 Japan

Yasuhiko TAKEMURA
Flat Atsugi 208, 931-1, Hase
Atsugi-shi, Kanagawa-ken, 243 Japan

CITIZENSHIP: Japan (all)

TITLE: SEMICONDUCTOR MATERIAL AND METHOD FOR FORMING
THE SAME AND THIN FILM TRANSISTOR

ASSIGNEE(S): Semiconductor Energy Laboratory Co., Ltd.
Kanagawa-ken, 243 Japan

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Sixbey, Friedman, Leedom & Ferguson, P.C.
2010 Corporate Ridge, Suite 600
McLean, Virginia 22102
(703) 790-9110